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Reg. No.....

Name.....

M.TECH. DEGREE EXAMINATION, JANUARY 2015

First Semester

Branch: Electronics and Communication Engineering

Specialisation—VLSI and Embedded Systems

MECVE 101—SEMICONDUCTOR DEVICES-PHYSICS AND MODELLING

(New Scheme-2013 Admission onwards)

[Regular/Improvement/Supplementary]

Time: Three Hours

Maximum: 100 Marks

Answer all questions. Each full question carries 25 marks.

1. (a) Define MOS transistor. Explain the structure and operation of MOS transistor in detail.

(15 marks)

(b) What is meant by inversion? Explain the various types of inversions.

(10 marks)

Or

- 2. Write short notes on:
 - (i) MOS capacitor;
 - (ii) Flat band voltage;
 - (iii) Potential balance and charge balance;
 - (iv) Flat band condition.

(25 marks)

3. (a) Compare body referenced and source referenced modelling.

(10 marks)

(b) Discuss the effects of extrinsic source and drain series resistances in detail.

(15 marks)

Or

4. Explain regions of inversion of the three terminal MOS structure in detail.

(25 marks)

5. (a) Write down the limitations of the quasi-static model.

(10 marks)

(b) Derive the continuity equation and explain the analysis of non-quasi-static modelling.

(15 marks)

6. I	Explain in de	tail				
	(a) Carri	er velocity saturation;	(b)	Channel length modulation;		
	(c) Hot c	arrier effects ;	(d)	Impact ionization.	No.	
				First San	(28	5 marks)
7. (a) Explain t	he following in detail:-		Branch : Electromes and Om		
	(a) BS	SIM;	lming)	Speculination-VLS1 and		۲.
	(b) EI	ELECTION IN THE		101—SEMICERADUCTOR DEV		
	(c) PS	SP.		KERN-scheduler will		
			więquikla	manyaqui halamili	(1	5 marks)
(b) Explain v	white noise and flicker i	oise in d	etail.	(10	0 marks)

8. (a) Compare the small signal capacitances at weak inversion, strong inversion (linear and saturation).

Street information (for arrestore and opposite

Or

(15 marks)

(b) Categories MOSFET simulation models.

(10 marks)

 $[4 \times 25 = 100 \text{ marks}]$

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Reg. No	
Name	

M.TECH. DEGREE EXAMINATION, JANUARY 2015

First Semester

Branch: Electronics and Communication Engineering

Specialisation—VLSI and Embedded Systems

MECVE 103—CMOS DIGITAL DESIGN I

(New Scheme—2013 Admission onwards)

[Regular/Improvement/Supplementary]

Time: Three Hours

Maximum: 100 Marks

Answer all questions. Each full question carries 25 marks.

1. (a) Explain gate diffusion capacitance in detail.

(15 marks)

(b) Discuss the transient response and Elmore delay.

(10 marks)

2. (a) With a suitable example discuss how the logical effort can be effectively used to estimate the multistage delay of a logical network. (15 marks)

- (b) Design and explain an inverter using:
 - (i) NMOS;
 - (ii) CMOS;
 - (iii) Pseudo NMOS.

(10 marks)

Explain cross talk control in detail.

(25 marks)

- 4. (a) Write a short note on:
 - (i) Inductive effects;
 - (ii) Skin effect;
 - (iii) Elmore delay.

(15 marks)

(b) Write a short note on inductive voltage fluctuation along the power lines? How this effect can be minimized in submicron technology.

(10 marks)

Turn over

 $[4 \times 25 = 100 \text{ marks}]$

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5. (a) Discuss and derive the floating body voltage. (10 marks) (b) Explain the structure of SOI inverter-Write down its advantages. (15 marks) Or 6. Explain in detail: Dual-rail Domino logic; Power dissipation in CMOS circuits. (25 marks) 7. (a) Explain design for manufacturability. (10 marks) (b) Explain in detail about: (i) Regularity (ii) Modularity; (iii) Software radio. 8. (a) How Kernighan-Lin algorithm can be used for partitioning? Explain with a suitable example. (15 marks) (b) Compare full custom and semi-custom. (10 marks)

(b) - Wiftin a three notes not specially a printing flowless than along the proper lines? How they refer than the

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Reg. No
Name

M.TECH. DEGREE EXAMINATION, JANUARY 2015

First Semester

Branch: Electronics and Communication

Specialization: VLSI and Embedded Systems

MECVE 104—EMBEDDED SYSTEM HARDWARE ARCHITECTURE—I

(New Scheme—2013 Admission onwards)

(1404) 5022	
[Regular / Improvement / Supplementary]	Maximum : 100 Marks
	Waximum . 100 1.201
Time: Three Hours	ks.
Time: Three Hours Answer all questions. Each full question carries 25 marks.	rems. (15 marks)
that must be present in the embedded system	011151
1. (a) List the hardware units that must be prosent (b) Explain the Exemplary applications of each type of embedded syst	em. (10 maria)
(b) Explain the Exemplary approximation Or	
	(15 marks)
2. (a) Explain the major components of an embedded board in detail.	(10 marks)
the term of processor.	(15 marks)
l slein the yen Neumann model.	(10 marks)
3. (a) Draw and explain the von Yestana and explain the hardware.	(10 marks)
(b) Discuss the powering the hardware. Or	
	(25 marks)
4. Explain embedded processor in detail.	(25 marks)
5. Explain memory systems in detail.	
5. Explain memory system Or	(a = -1-a)
we are of external memory.	(15 marks)
6. (a) Discuss the memory management of external memory.	(10 marks)
(b) Explain the board of memory and interface.	I in IEEE 802.11?
(b) Explain the board of memory and interface.7. (a) What is PIF, DIF and SIF time intervals and how they are used	(15 marks)
1. (a) 11240 -	(10 marks)
(b) Discuss in detail about SPI.	ì
(b) Discuss in detail about 22 30 Or	1 -
77.1.7/0	(10 marks)
8. (a) Compare serial and parallel I/O.	(15 marks)
(b) Explain the board buses in detail.	$[4 \times 25 = 100 \text{ marks}]$
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M.TECH. DEGREE EXAMINATION, JANUARY 2015

First Semester

Branch: Electronics and Communication Engineering

Specialization: VLSI and Embedded Systems

MECVE 106-1 VLSI CAD

(New Scheme-2013 Admission onwards)

[Regular/Improvement/Supplementary]

Time: Three Hours

Maximum: 100 Marks

Answer all questions.

Each full question carries 25 marks.

- 1. (a) Explain in detail about the VLSI design cycle.
 - (b) Briefly explain the problem formulation.

(12 + 13 = 25 marks)

Or

- 2. (a) Explain the applications of compaction.
 - (b) Explain the longest path algorithm for DAGs.

(12 + 13 = 25 marks)

- 3. (a) Explain the types of placement problem.
 - (b) Explain in detail about the placement algorithms.

(12 + 13 = 25 marks)

Or

- 4. (a) Briefly explain the Kerlinghan-Lin partioning algorithm.
 - (b) Explain the circuit representation and wire length estimation.

(12 + 13 = 25 marks)

- 5. (a) Discuss in detail about the floor planning algorithms.
 - (b) Briefly explain the Hierarchical partitioning.

(12 + 13 = 25 marks)

- 6. (a) Describe the dead soaces in detail.
 - (b) Discuss the slicing and non-slicing and state the applications.

(12 + 13 = 25 marks)

- 7. (a) State the types of local routing problems.
 - (b) Explain the significance of area routing.

(15 + 10 = 25 marks)

- 8. (a) State the importance of routing and its merits and issues...
 - (b) Write in detail about the taxonomy on VLSI routers.

(15 + 10 = 25 marks)

 $[4 \times 25 = 100 \text{ marks}]$

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(12 = 13 = 20 starles).

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and defectly explice the party of the property of

(b) Delete acquire use the gradient partitioning

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